



STP12PF06

P - CHANNEL 60V - 0.18 Ω - 12A TO-220 STripFET™ POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STP12PF06	60 V	< 0.20 Ω	12 A

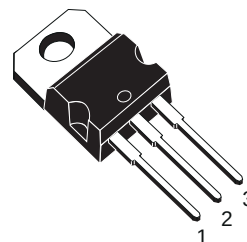
- TYPICAL R_{DS(on)} = 0.18 Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- LOW GATE CHARGE
- APPLICATION ORIENTED CHARACTERIZATION

DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

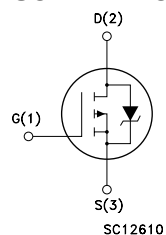
APPLICATIONS

- MOTOR CONTROL
- DC-DC & DC-AC CONVERTERS



TO-220

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	60	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 k Ω)	60	V
V _{GS}	Gate-source Voltage	± 20	V
I _D	Drain Current (continuous) at T _c = 25 °C	12	A
I _D	Drain Current (continuous) at T _c = 100 °C	8.4	A
I _{DM} (•)	Drain Current (pulsed)	48	A
P _{tot}	Total Dissipation at T _c = 25 °C	60	W
	Derating Factor	0.4	W/°C
dv/dt	Peak Diode Recovery voltage slope	6	V/ns
T _{stg}	Storage Temperature	-65 to 175	°C
T _j	Max. Operating Junction Temperature	175	°C

(•) Pulse width limited by safe operating area

(1) I_{SD} ≤ 12 A, di/dt ≤ 300 A/ μ s, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}

Note: For the P-CHANNEL MOSFET actual polarity of voltages and current has to be reversed

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	2.5	$^{\circ}C/W$
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	62.5	$^{\circ}C/W$
$R_{thc-sink}$	Thermal Resistance Case-sink	Typ	0.5	$^{\circ}C/W$
T_I	Maximum Lead Temperature For Soldering Purpose		275	$^{\circ}C$

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	12	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25^{\circ}C$, $I_D = I_{AR}$, $V_{DD} = 25V$)	200	mJ

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250 \mu A$ $V_{GS} = 0$	60			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$ $T_c = 125^{\circ}C$			1 10	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20 V$			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250 \mu A$	2	3.4	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10V$ $I_D = 6 A$		0.18	0.20	Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10 V$	12			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (*)$	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 6 A$	2.5	6		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25 V$ $f = 1 MHz$ $V_{GS} = 0$		850 230 75		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 30\text{ V}$ $I_D = 6\text{ A}$		20		ns
t_r	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (Resistive Load, see fig. 3)		40		ns
Q_g	Total Gate Charge	$V_{DD} = 48\text{ V}$ $I_D = 12\text{ A}$ $V_{GS} = 10\text{ V}$		16	21	nC
Q_{gs}	Gate-Source Charge			4		nC
Q_{gd}	Gate-Drain Charge			6		nC

SWITCHING OFF

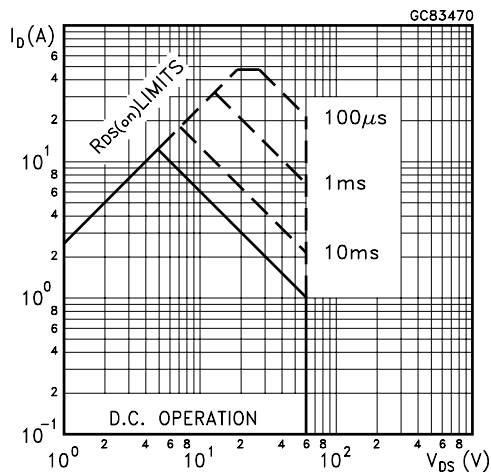
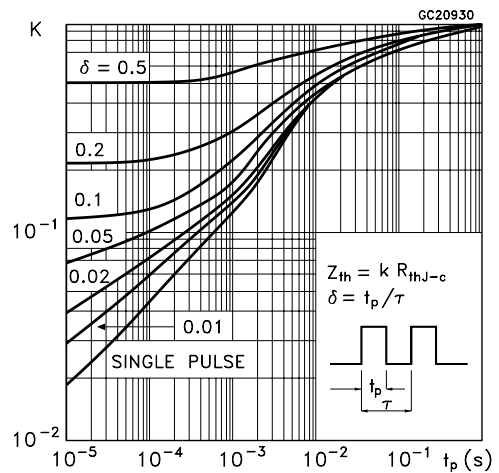
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off Delay Time	$V_{DD} = 30\text{ V}$ $I_D = 6\text{ A}$		40		ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (Resistive Load, see fig. 3)		10		ns
$t_{r(voff)}$	Off-voltage Rise Time	$V_{DD} = 48\text{ V}$ $I_D = 12\text{ A}$		10		ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		17		ns
t_c	Cross-over Time	(Inductive Load, see fig. 5)		30		ns

SOURCE DRAIN DIODE

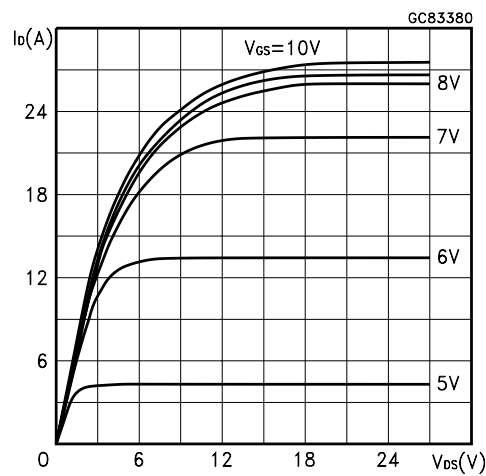
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				10	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				40	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 12\text{ A}$ $V_{GS} = 0$			2.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 12\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_J = 150\text{ }^\circ\text{C}$ (see test circuit, fig. 5)		100		ns
Q_{rr}	Reverse Recovery Charge			260		nC
I_{RRM}	Reverse Recovery Current			5.2		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

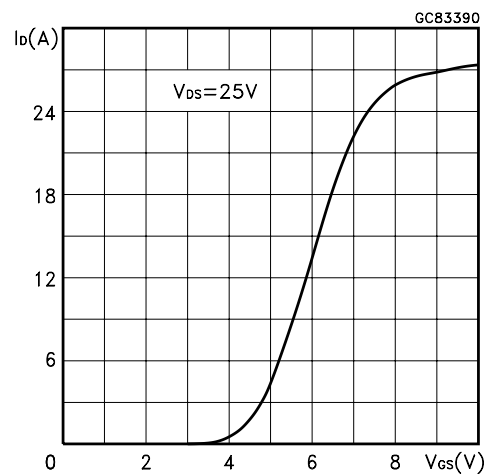
(\bullet) Pulse width limited by safe operating area

Safe Operating Area**Thermal Impedance**

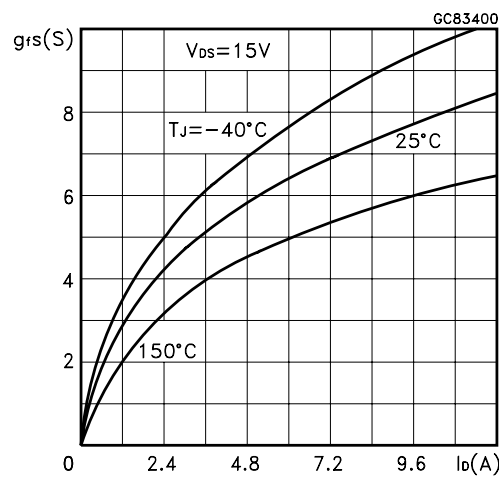
Output Characteristics



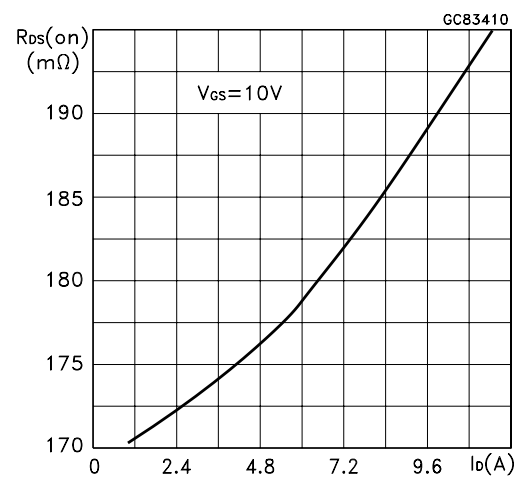
Transfer Characteristics



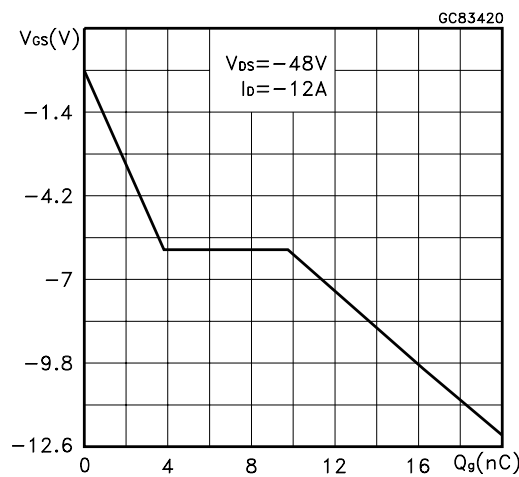
Transconductance



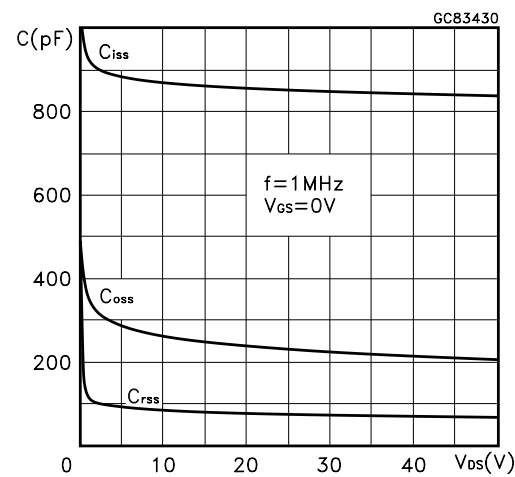
Static Drain-source On Resistance



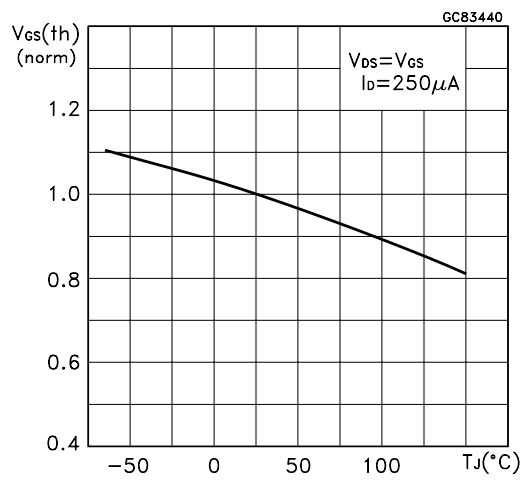
Gate Charge vs Gate-source Voltage



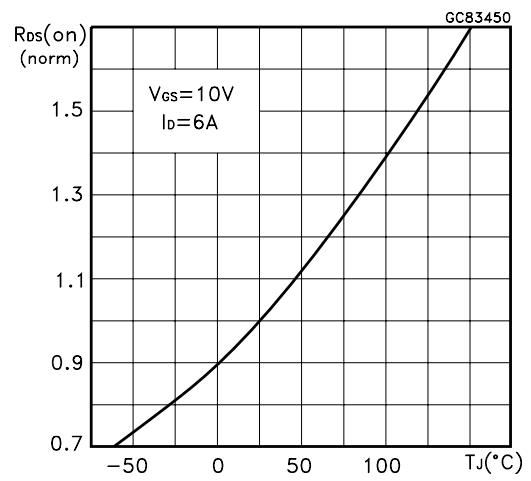
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

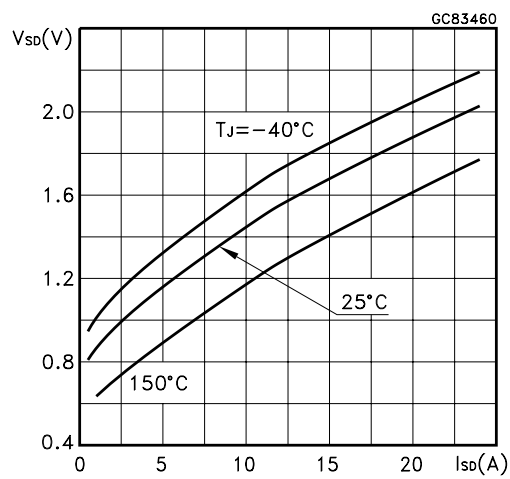


Fig. 1: Unclamped Inductive Load Test Circuit

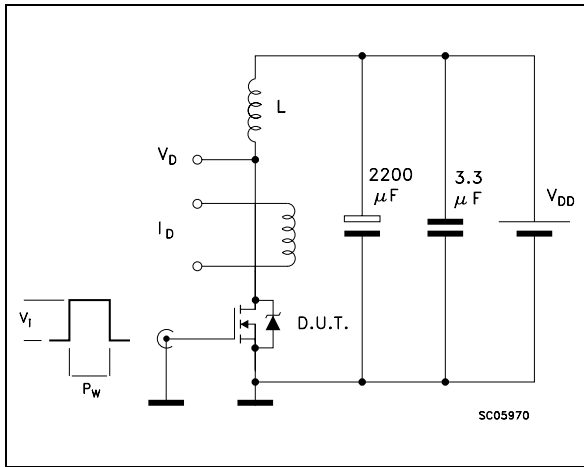


Fig. 2: Unclamped Inductive Waveform

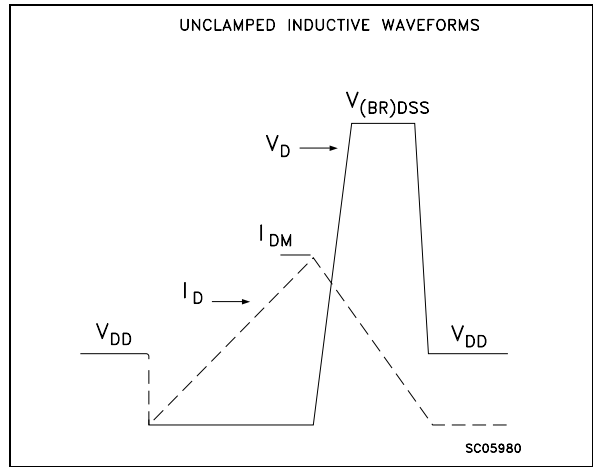


Fig. 3: Switching Times Test Circuits For Resistive Load

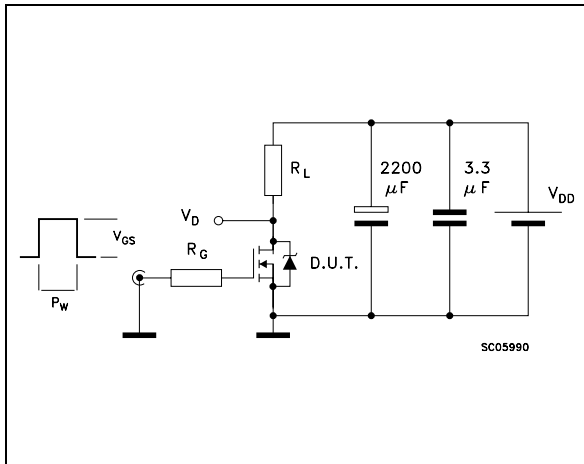


Fig. 4: Gate Charge test Circuit

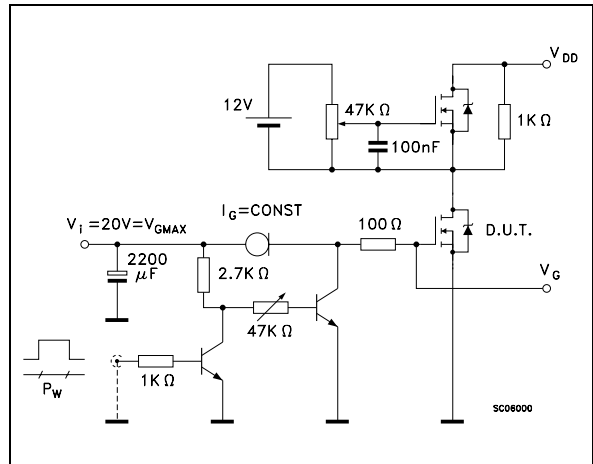
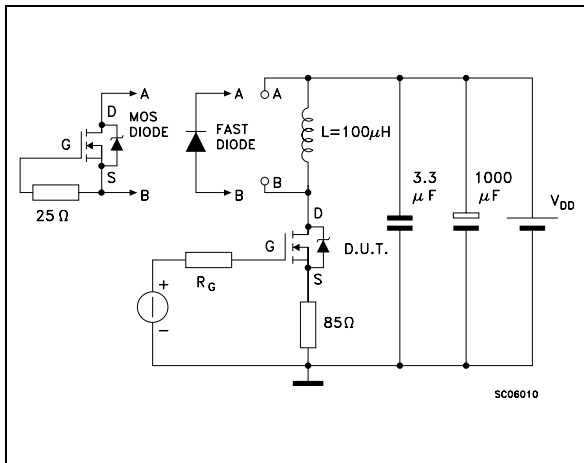
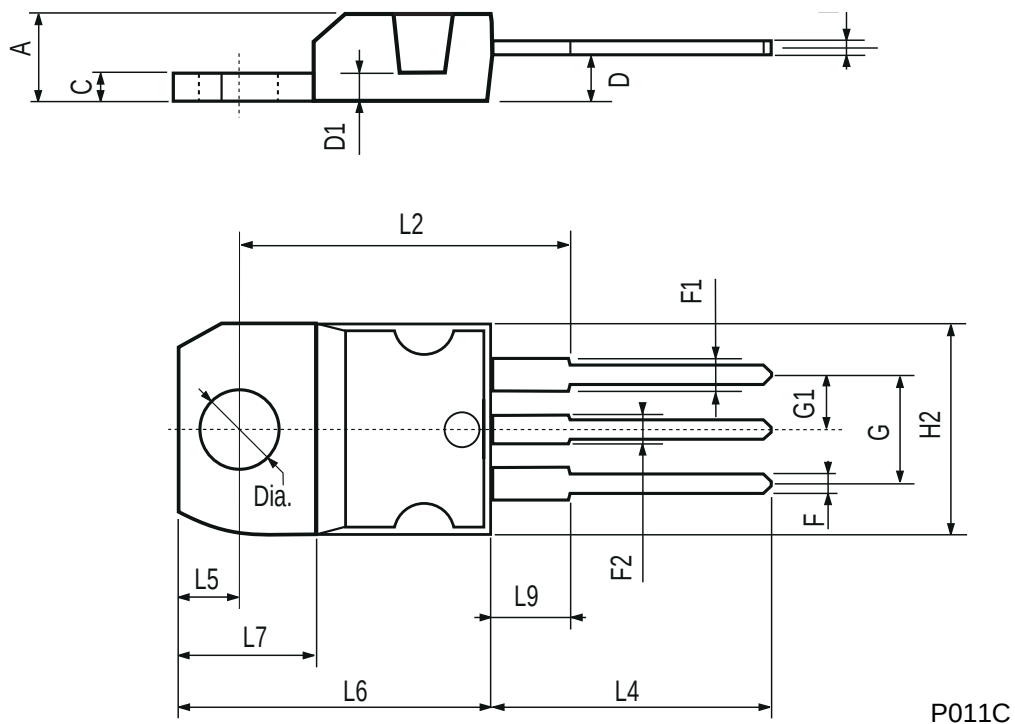


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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